

# BD243B, BD243C (NPN) BD244B, BD244C (PNP)



ON Semiconductor®

<http://onsemi.com>

## Complementary Silicon Plastic Power Transistors

These devices are designed for use in general purpose amplifier and switching applications.

### Features

- Collector – Emitter Saturation Voltage –  
 $V_{CE(sat)} = 1.5 \text{ Vdc (Max) @ } I_C = 6.0 \text{ Adc}$
- Collector Emitter Sustaining Voltage –  
 $V_{CEO(sus)} = 80 \text{ Vdc (Min) – BD243B, BD244B}$   
 $= 100 \text{ Vdc (Min) – BD243C, BD244C}$
- High Current Gain Bandwidth Product  
 $f_T = 3.0 \text{ MHz (Min) @ } I_C = 500 \text{ mAdc}$
- Pb-Free Packages are Available\*

**6 AMPERE  
POWER TRANSISTORS  
COMPLEMENTARY SILICON  
80–100 VOLTS  
65 WATTS**

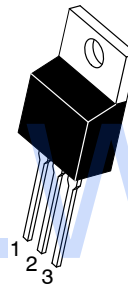
### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage BD243B, BD244B BD243C, BD244C	$V_{CEO}$	80 100	Vdc
Collector–Base Voltage BD243B, BD244B BD243C, BD244C	$V_{CB}$	80 100	Vdc
Emitter–Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current – Continuous – Peak	$I_C$	6 10	Adc
Base Current	$I_B$	2.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	65 0.52	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.92	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



TO-220AB  
CASE 221A-09  
STYLE 1

### MARKING DIAGRAM



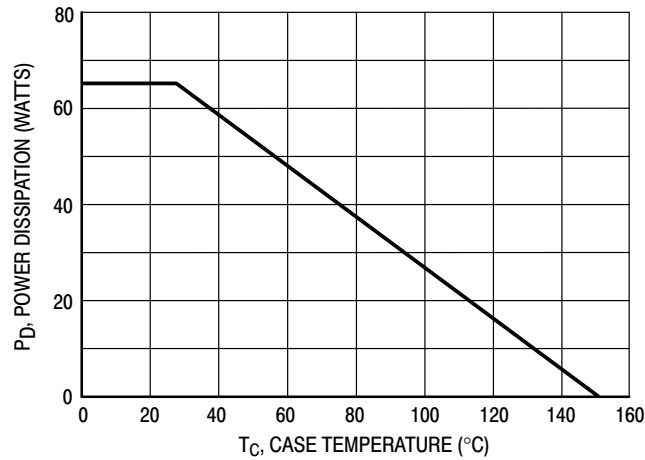
BD24xy = Device Code  
x = 3 or 4  
y = B or C  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## BD243B, BD243C (NPN) BD244B, BD244C (PNP)



**Figure 1. Power Derating**

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector–Emitter Sustaining Voltage (Note 1) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	80 100	– –	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	–	0.7	mAdc
Collector Cutoff Current (V <sub>CE</sub> = 80 Vdc, V <sub>EB</sub> = 0) (V <sub>CE</sub> = 100 Vdc, V <sub>EB</sub> = 0)	I <sub>CES</sub>	– –	400 400	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	1.0	mAdc

### ON CHARACTERISTICS (Note 1)

DC Current Gain (I <sub>C</sub> = 0.3 Adc, V <sub>CE</sub> = 4.0 Vdc) (I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	h <sub>FE</sub>	30 15	– –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 6.0 Adc, I <sub>B</sub> = 1.0 Adc)	V <sub>CE(sat)</sub>	–	1.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 6.0 Adc, V <sub>CE</sub> = 4.0 Vdc)	V <sub>BE(on)</sub>	–	2.0	Vdc

### DYNAMIC CHARACTERISTICS

Current–Gain – Bandwidth Product (Note 2) (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)	f <sub>T</sub>	3.0	–	MHz
Small–Signal Current Gain (I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	20	–	–

1. Pulse Test: Pulsewidth ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. f<sub>T</sub> = h<sub>fe</sub> • f<sub>test</sub>

# BD243B, BD243C (NPN) BD244B, BD244C (PNP)

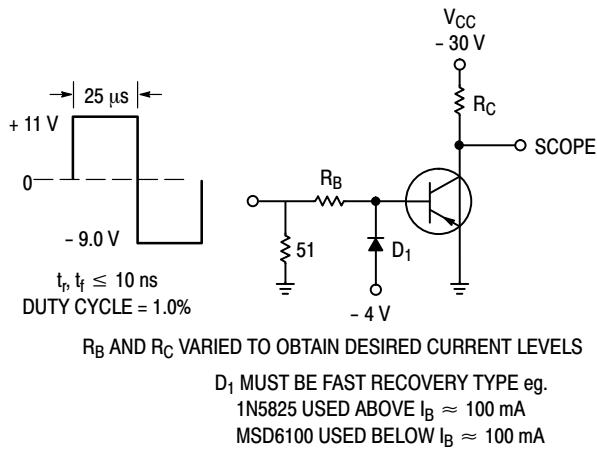


Figure 2. Switching Time Test Circuit

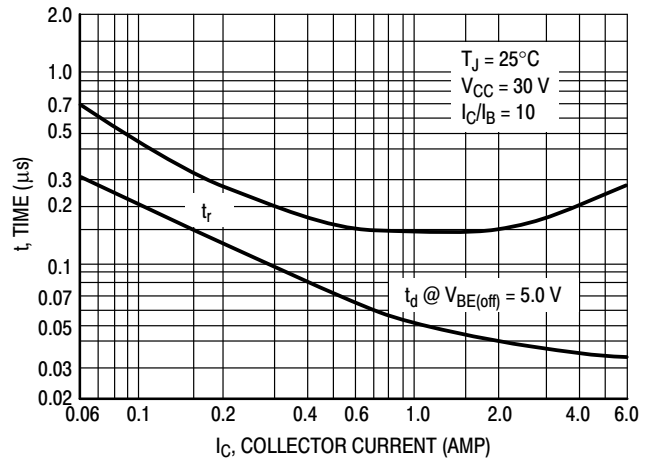


Figure 3. Turn-On Time

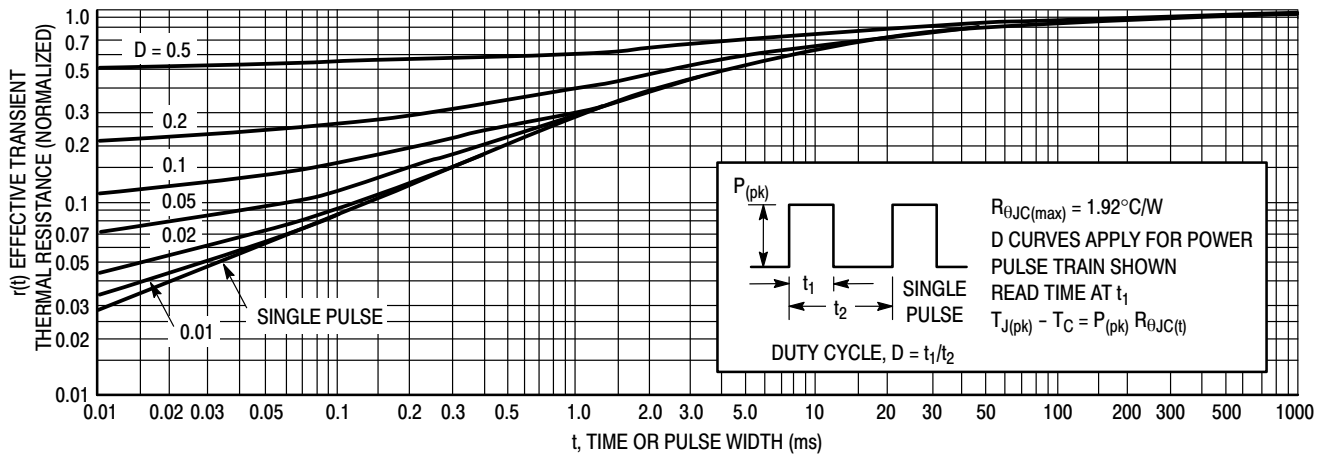


Figure 4. Thermal Response

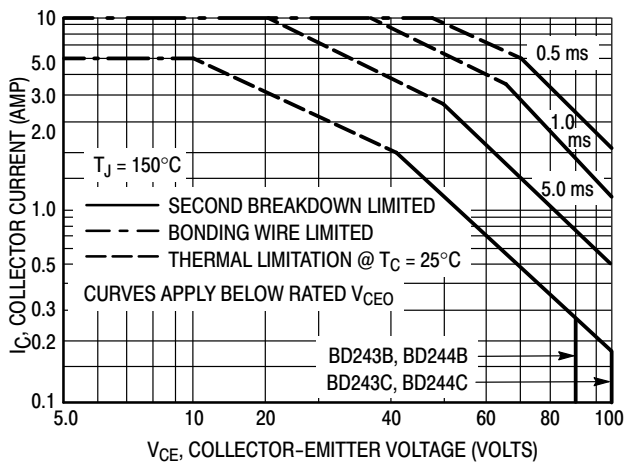
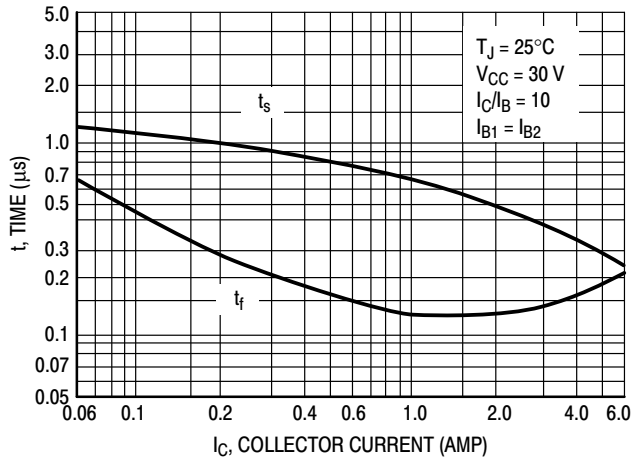


Figure 5. Active Region Safe Operating Area

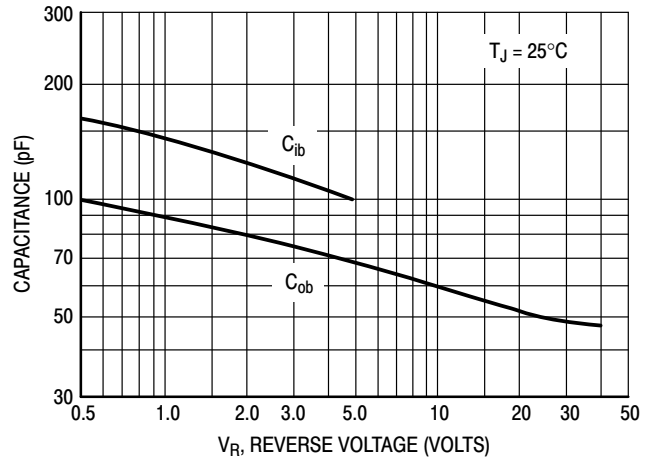
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^\circ\text{C}$ :  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ ,  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

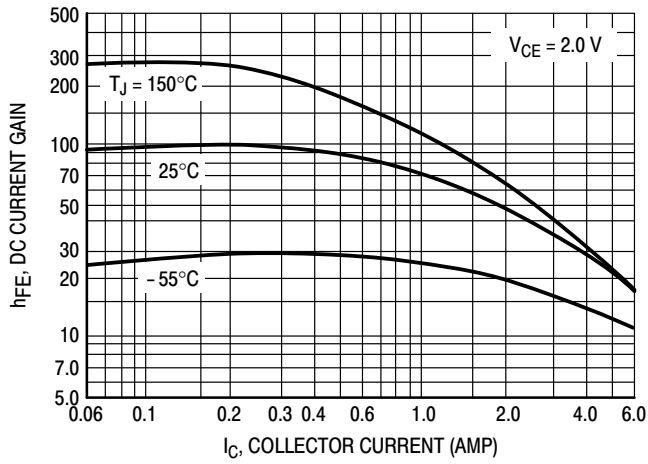
# BD243B, BD243C (NPN) BD244B, BD244C (PNP)



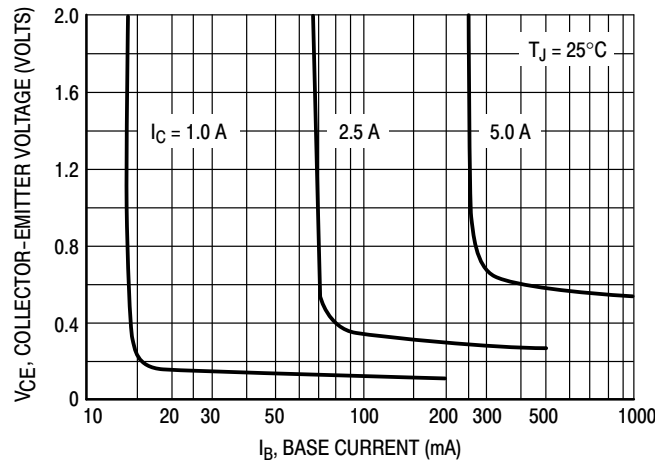
**Figure 6. Turn-Off Time**



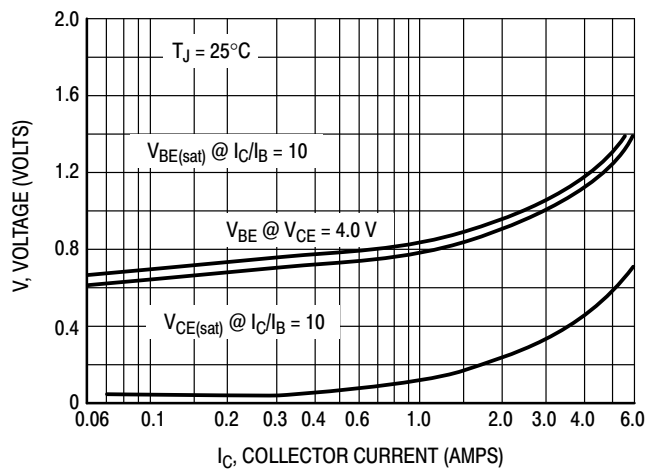
**Figure 7. Capacitance**



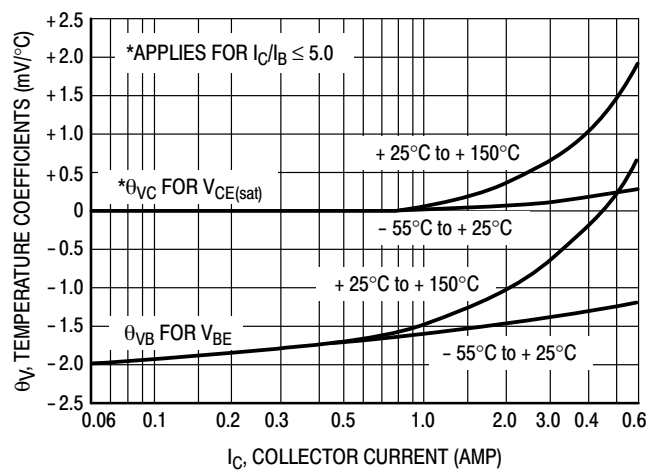
**Figure 8. DC Current Gain**



**Figure 9. Collector Saturation Region**

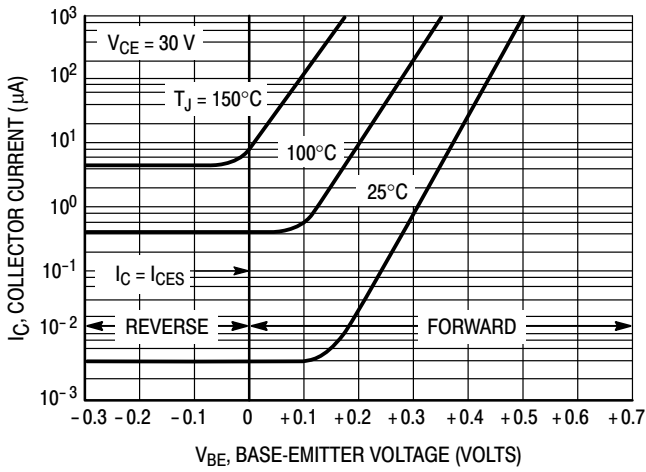


**Figure 10. "On" Voltages**

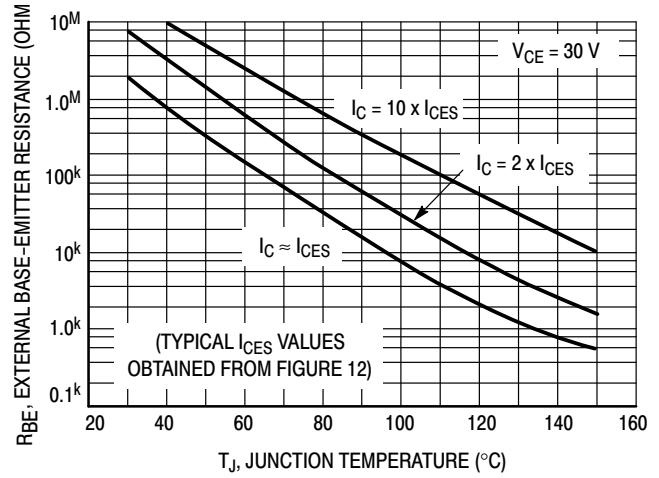


**Figure 11. Temperature Coefficients**

## BD243B, BD243C (NPN) BD244B, BD244C (PNP)



**Figure 12. Collector Cut-Off Region**



**Figure 13. Effects of Base-Emitter Resistance**

### ORDERING INFORMATION

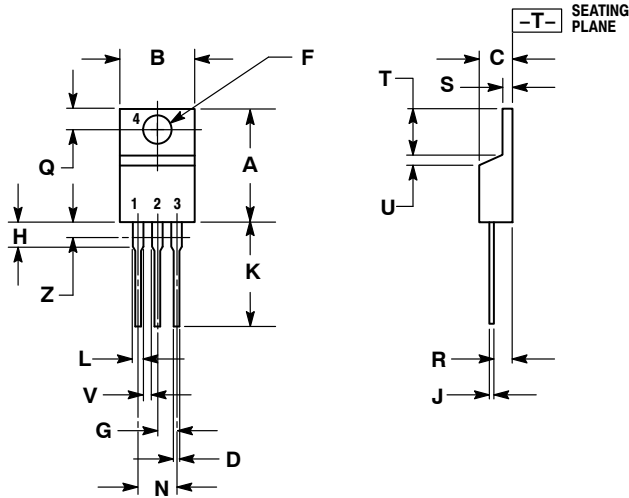
Device	Package	Shipping†
BD243B	TO-220	50 Units / Rail
BD243BG	TO-220 (Pb-Free)	
BD243C	TO-220	50 Units / Rail
BD243CG	TO-220 (Pb-Free)	
BD244B	TO-220	50 Units / Rail
BD244BG	TO-220 (Pb-Free)	
BD244C	TO-220	50 Units / Rail
BD244CG	TO-220 (Pb-Free)	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BD243B, BD243C (NPN) BD244B, BD244C (PNP)

## PACKAGE DIMENSIONS

TO-220  
CASE 221A-09  
ISSUE AG



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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